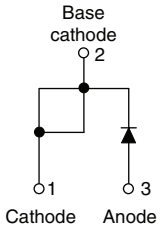
HEXFRED®
Ultrafast Soft Recovery Diode, 8 A



TO-220AC

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating conditions
- Lead (Pb)-free
- Designed and qualified for industrial level

Pb Available

RoHS* COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

HFA08TB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A continuous current, the HFA08TB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08TB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRODUCT SUMMARY	
V_R	600 V
V_F at 8 A at 25 °C	1.7 V
$I_{F(AV)}$	8 A
t_{rr} (typical)	18 ns
T_J (maximum)	150 °C
Q_{rr} (typical)	65 nC
$dI_{(rec)M}/dt$ (typical)	240 A/µs
I_{RRM}	5.0 A

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Cathode to anode voltage	V_R		600	V
Maximum continuous forward current	I_F	T_C = 100 °C	8	A
Single pulse forward current	I_{FSM}		60	
Maximum repetitive forward current	I_{FRM}		24	
Maximum power dissipation	P_D	T_C = 25 °C	36	W
		T_C = 100 °C	14	
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C

* Pb containing terminations are not RoHS compliant, exemptions may apply

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		600	-	-	V
Maximum forward voltage	V_{FM}	I_F = 8.0 A	See fig. 1	-	1.4	1.7	
		I_F = 16 A		-	1.7	2.1	
		I_F = 8.0 A, T_J = 125 °C		-	1.4	1.7	
Maximum reverse leakage current	I_{RM}	$V_R = V_R$ rated	See fig. 2	-	0.3	5.0	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated		-	100	500	
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	10	25	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	18	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 8.0 A dI_F/dt = 200 A/µs V_R = 200 V	-	37	55	
	t_{rr2}	T_J = 125 °C		-	55	90	
Peak recovery current	I_{RRM1}	T_J = 25 °C		-	3.5	5.0	A
	I_{RRM2}	T_J = 125 °C		-	4.5	8.0	
Reverse recovery charge	Q_{rr1}	T_J = 25 °C		-	65	138	nC
	Q_{rr2}	T_J = 125 °C		-	124	360	
Peak rate of fall of recovery current during t_b	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	240	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	210	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	3.5	K/W
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	80	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-220AC	HFA08TB60			

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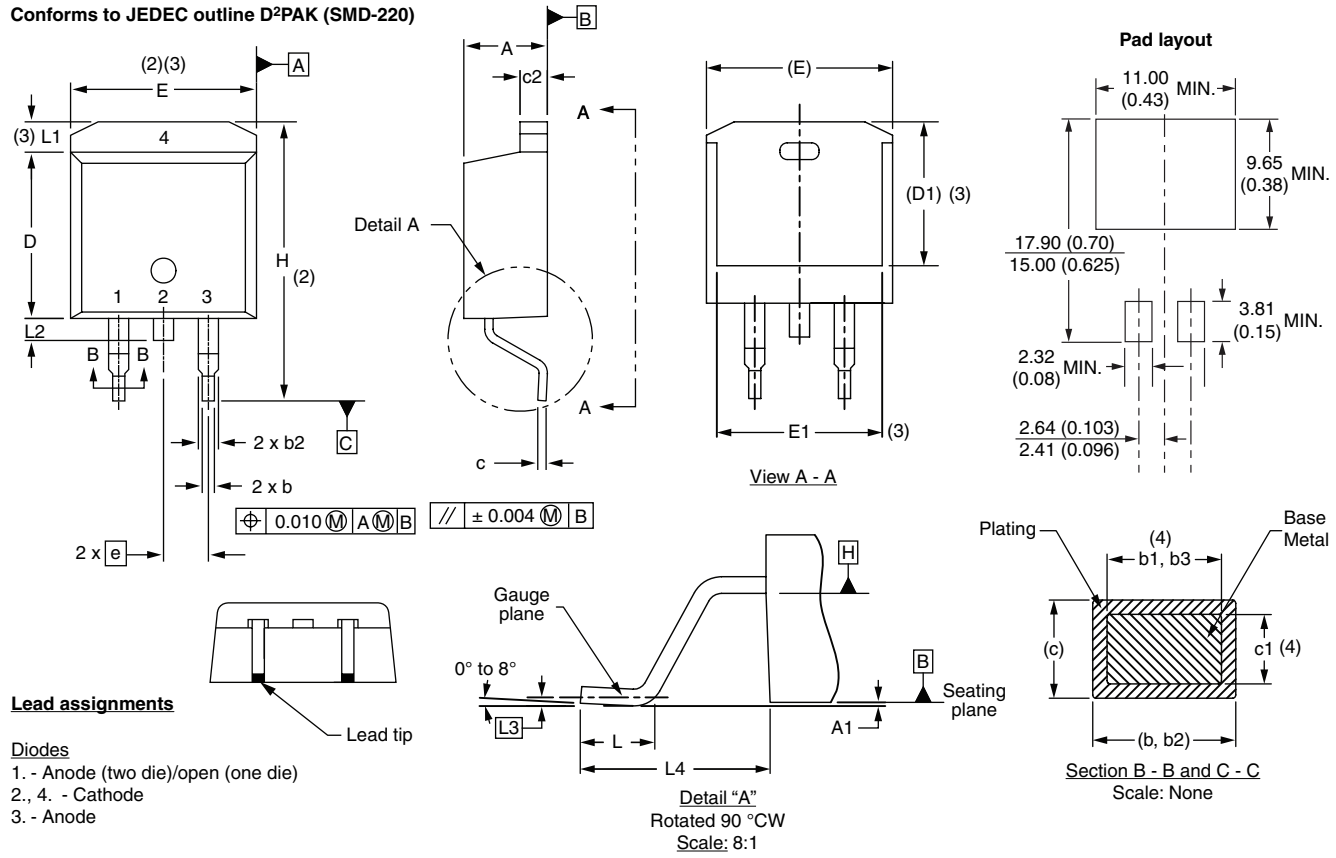
DIMENSIONS in millimeters and inches



Lead assignments

Diodes
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
c	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D1	6.86	-	0.270	-	3
E	9.65	10.67	0.380	0.420	2, 3
E1	6.22	-	0.245	-	3
e	2.54 BSC		0.100 BSC		
H	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

(1) Dimensioning and tolerancing per ASME Y14.5 M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
(3) Thermal pad contour optional within dimension E, L1, D1 and E1
(4) Dimension b1 and c1 apply to base metal only
(5) Datum A and B to be determined at datum plane H
(6) Controlling dimension: inch
(7) Outline conforms to JEDEC outline TO-263AB

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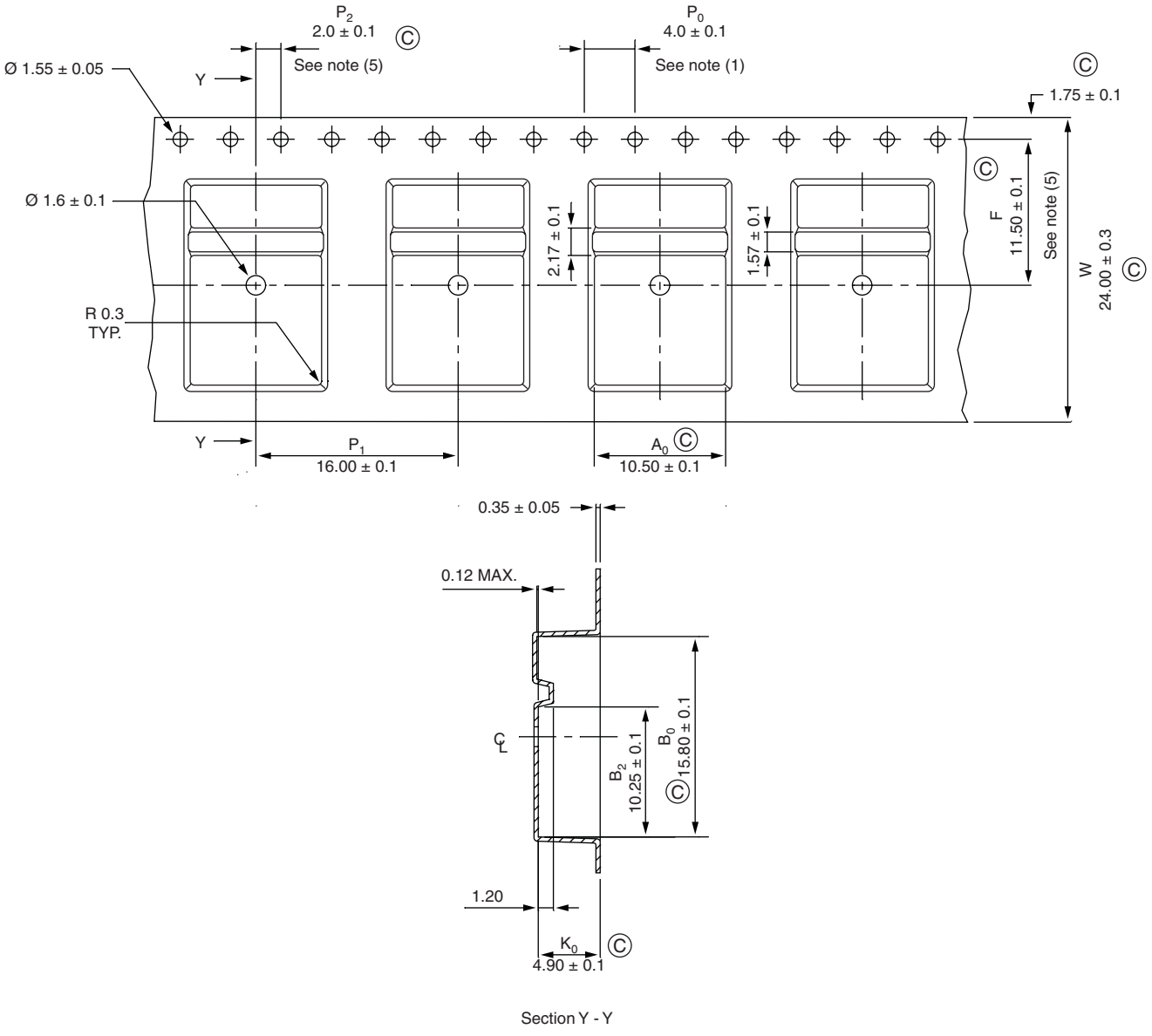
TAPE AND REEL INFORMATION in millimeters (inches)



Section Y - Y

Notes

(1) 10 sprocket hole pitch cumulative tolerance ± 0.02
(2) Camber not to exceed 1 mm in 100 mm
(3) Material: conductive black styrenic alloy
(4) K_0 measured from a plane on the inside bottom of the pocket to the top surface of the carrier
(5) Measured from centerline of sprocket hole to centerline of pocket
(6) Vendor: (optional)
(7) Must also meet requirements of EIA standard # EIA-481A taping of surface mount components for automatic placement
(8) Surface resistivity of molded material must measure less or equal to 10^6 Ω per square. Measured in accordance to procedure given in ASTM D-257 and ASTM D-991
(9) Total length per reel must be 45 m
(10) Ⓒ critical